



Product data sheet

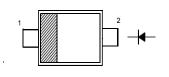
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Surface Mount Schottky Barrier Diodes

Features

Low Forward Voltage



MARK:

PINNING	
PIN	DESCRIPTION
1	Cathode
2	Anode

SD103AWT:S4	SD103BWT:S4	SD103CWT:S6
1	¹ S5 ²	¹ S6 ²

Absolute Maximum Ratings (T_a = 25 °C)

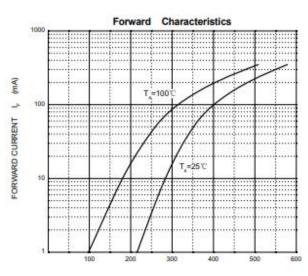
Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage	SD103AWT SD103BWT SD103CWT	V _{RRM}	40 30 20	V
Reverse Voltage	SD103AWT SD103BWT SD103CWT	V _R	40 30 20	V
Average Forward Rectified Current		I _{F(AV)}	350	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s		I _{FSM}	2	А
Power Dissipation		P _{tot}	200	mW
Operating and Storage Temperature Range	9	T _j , T _{stg}	- 65 to + 125	°C

Characteristics at T_a = 25 °C

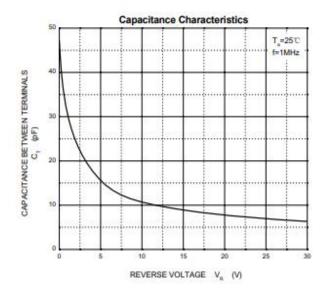
Parameter		Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage						
at I _R =10uA	SD103AWT	V _{(BR)R}	40	-	-	v
	SD103BWT		30	-	-	v
	SD103CWT		20	-	-	
Reverse Leakage Current						
at V _R =30V	SD103AWT	I _R	-	-	5	
at V _R = 20 V	SD103BWT		-	-	5	μA
at V _R = 10 V	SD103CWT		-	-	5	
Forward Voltage						
at I _F = 20 mA		VF	-	-	0.37	V
at I _F = 200 mA			-	-	0.6	
Total Capacitance				50		Ē
at $V_R = 0$ V, f = 1 MHz		C⊤	-	50	-	pF
Reverse Recovery Time		4		10		
at I _F = I _R = 200 mA, I _{rr} = 0.1 I _R , R _L = 100 Ω		t _{rr}	-	10	-	ns

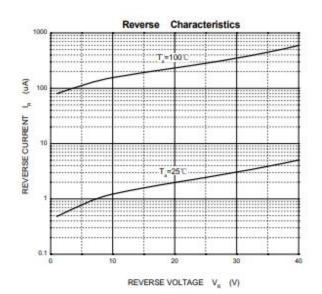


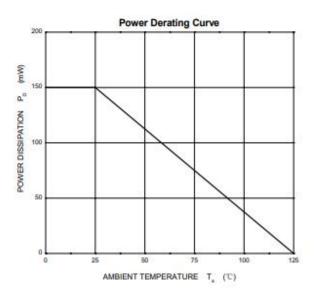
Typical Characteristics



FORWARD VOLTAGE V_F (mV)



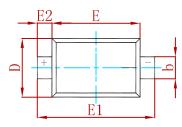


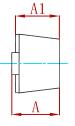


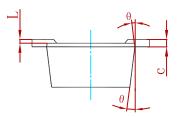


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PACKAGE MECHANICAL DATA

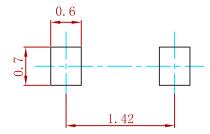






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	0.510	0.770	0.020	0.031	
A1	0.500	0.700	0.020	0.028	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	0.750	0.850	0.030	0.033	
E	1.100	1.300	0.043	0.051	
E1	1.500	1.700	0.059	0.067	
E2	0.200 REF		300.0	B REF	
L	0.010	0.070	0.001	0.003	
θ	7° REF		7° F	REF	

Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SD103AWT/SD103BWT/SD103CWT	SOD-523	3000



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